Product data sheet

1. Product profile

1.1 General description

Planar Schottky barrier single diode with an integrated guard ring for stress protection, encapsulated in a SOD323F (SC-90) very small and flat lead Surface-Mounted Device (SMD) plastic package.

1.2 Features

- Low forward voltage
- Very small and flat lead SMD plastic package
- Low capacitance
- Flat leads: excellent coplanarity and improved thermal behavior

1.3 Applications

- Voltage clamping
- Line termination
- Reverse polarity protection

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I _F	forward current		-	-	200	mA
V_R	reverse voltage		-	-	30	V
V_{F}	forward voltage	$I_F = 1 \text{ mA}$	<u>[1]</u> _	-	320	mV

[1] Pulse test: $t_p \le 300~\mu s;~\delta \le 0.02.$



Schottky barrier single diode

2. Pinning information

Table 2. Pinning

Pin	Description	Simplified outline	Symbol
1	cathode	[1]	. 84
2	anode	1 2	1 🕂 2
			sym001

^[1] The marking bar indicates the cathode.

3. Ordering information

Table 3. Ordering information

Type number	Package				
	Name	Description	Version		
BAT54J	SC-90	plastic surface-mounted package; 2 leads	SOD323F		

4. Marking

Table 4. Marking codes

Type number	Marking code
BAT54J	AP

5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_R	reverse voltage		-	30	V
I _F	forward current		-	200	mA
I _{FRM}	repetitive peak forward current	$t_p \le 1 \text{ s}; \ \delta \le 0.5$	-	300	mA
I _{FSM}	non-repetitive peak forward current	square wave; t _p < 10 ms	-	600	mA
P _{tot}	total power dissipation	$T_{amb} \le 25 ^{\circ}C$	<u>[1]</u> _	550	mW
Tj	junction temperature		-	150	°C
T _{amb}	ambient temperature		-65	+150	°C
T _{stg}	storage temperature		-65	+150	°C

^[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for cathode 1 cm².

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6. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1][2] _	-	230	K/W
$R_{th(j-sp)}$	thermal resistance from junction to solder point		<u>[3]</u> _	-	55	K/W

^[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for cathode 1 cm².

7. Characteristics

Table 7. Characteristics

 T_{amb} = 25 °C unless otherwise specified.

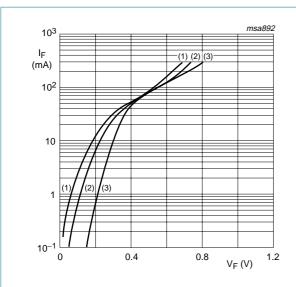
		-				
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{F}	forward voltage		<u>[1]</u>			
		$I_F = 0.1 \text{ mA}$	-	-	240	mV
		I _F = 1 mA	-	-	320	mV
		I _F = 10 mA	-	-	400	mV
		I _F = 30 mA	-	-	500	mV
		I _F = 100 mA	-	-	800	mV
I_R	reverse current	V _R = 25 V	-	-	2	μΑ
C_d	diode capacitance	$V_R = 1 V$; $f = 1 MHz$	-	-	10	pF

^[1] Pulse test: $t_p \le 300 \ \mu s; \ \delta \le 0.02$.

^[2] Reflow soldering is the only recommended soldering method.

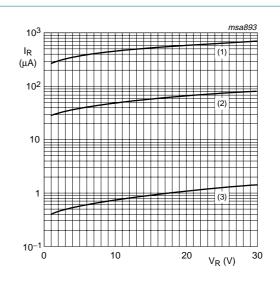
^[3] Soldering point of cathode tab.

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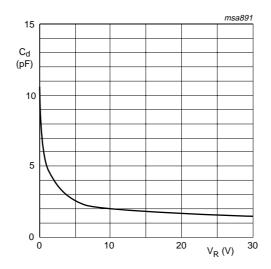
- (1) $T_{amb} = 125 \, ^{\circ}C$
- (2) $T_{amb} = 85 \, ^{\circ}C$
- (3) $T_{amb} = 25 \, ^{\circ}C$

Fig 1. Forward current as a function of forward voltage; typical values



- (1) $T_{amb} = 125 \, ^{\circ}C$
- (2) $T_{amb} = 85 \, ^{\circ}C$
- (3) $T_{amb} = 25 \, ^{\circ}C$

Fig 2. Reverse current as a function of reverse voltage; typical values

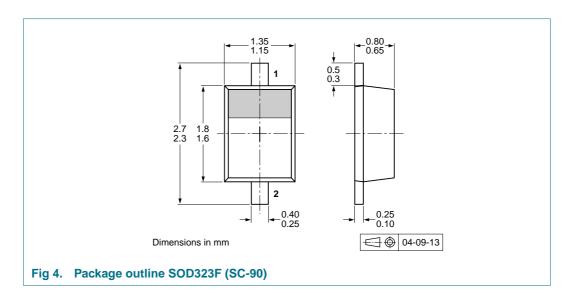


 T_{amb} = 25 °C; f = 1 MHz

Fig 3. Diode capacitance as a function of reverse voltage; typical values

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8. Package outline



9. Packing information

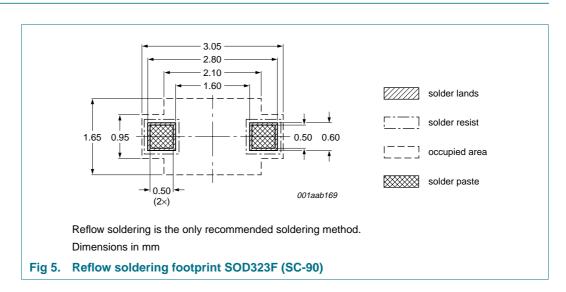
Table 8. Packing methods

The indicated -xxx are the last three digits of the 12NC ordering code.[1]

Type number	Package	Description	Packing qu	Packing quantity	
			3000	10000	
BAT54J	SOD323F	4 mm pitch, 8 mm tape and reel	-115	-135	

^[1] For further information and the availability of packing methods, see Section 13.

10. Soldering



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11. Revision history

Table 9. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BAT54J_1	20070308	Product data sheet	-	-

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12. Legal information

12.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
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